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(71)Applicant : TOYODA GOSEI CO LTD
(72)Inventor : SHIBATA NAOKI
SENDAI TOSHIAKI
SENDA MASANOBU
ITO JUN
WATANABE HIROSHI
ASAMI SHINYA
ASAMI SHIZUYO

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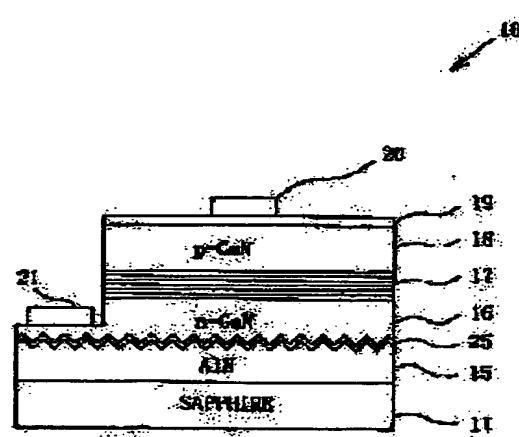
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(54) III NITRIDE COMPOUND SEMICONDUCTOR ELEMENT

(57)Abstract:

PROBLEM TO BE SOLVED: To substantially totally reflect a light from a III nitride compound semiconductor in a substrate layer having a textured structure, a sectional trapezoidal shape or a pit-like surface shape.

SOLUTION: A reflecting layer made of a nitride of one or more types of metals selected from titanium, zirconium, hafnium and tantalum is formed on the textured structure, sectional trapezoidal shape or the pit-like surface of the substrate layer. The surface structure of the substrate layer is reflected, and the surface of the reflecting layer is also the textured structure, the sectional trapezoidal shape or the pit-like state.



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